



# Industrial Application of n- Type Bifacial TOPCon Technology

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**Jolywood Solar Taizhou**

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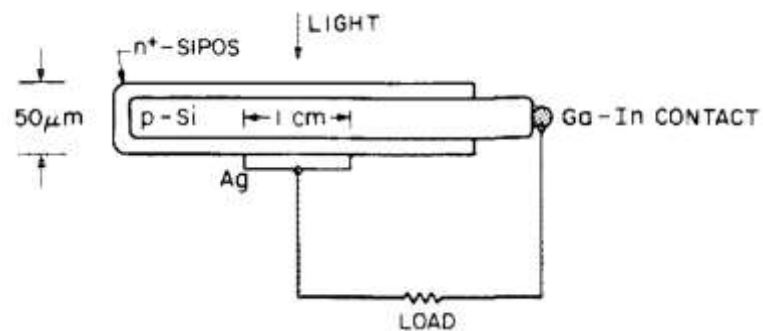
**Jolywood TOPCon 2.0 Product**

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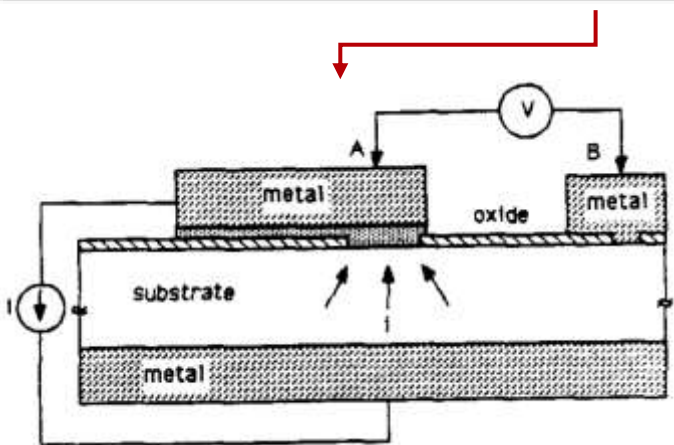
# History of TOPCon technology

1985, Stanford University  
SIPOS,  $V_{oc} \sim 720$  mV



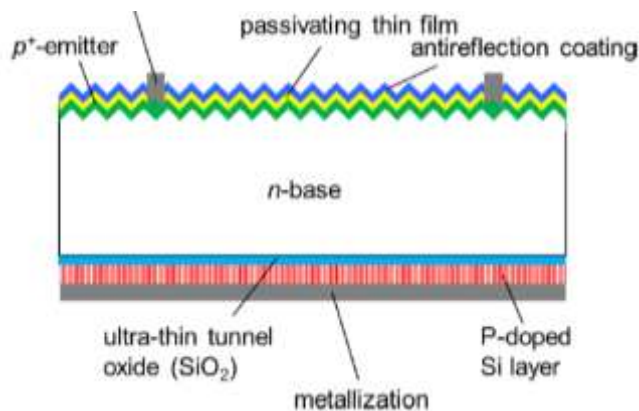
1985

1990



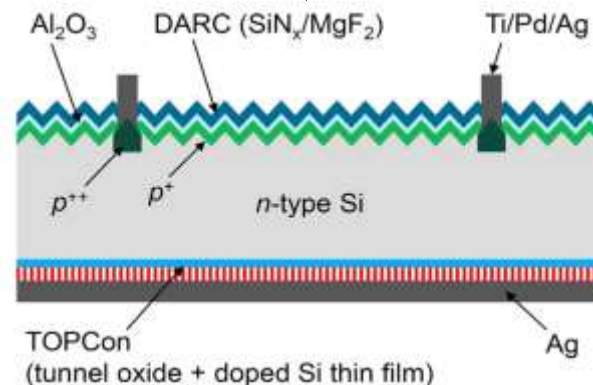
1990, Stanford University  
Poly-Si, low  $J_0$  and  $\rho_c$

2013, Fraunhofer ISE  
TOPCon,  $\eta \sim 23.02\%$



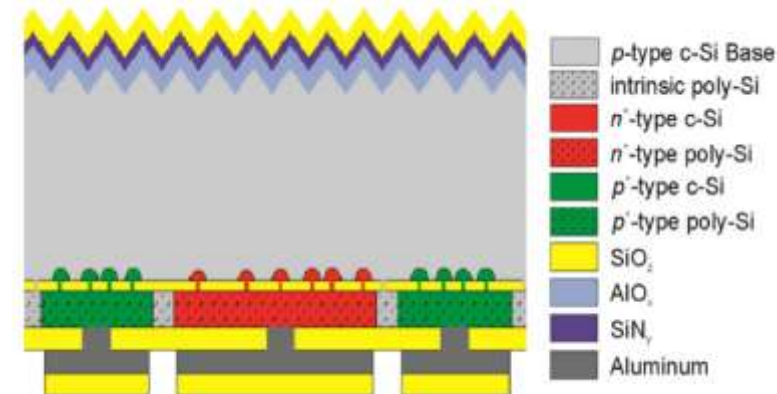
2013

2017



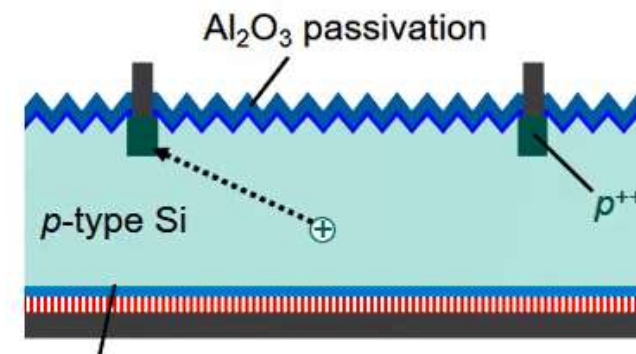
2017, Fraunhofer ISE  
TOPCon,  $\eta \sim 25.7\%$

2018, ISFH  
POLO-IBC,  $\eta \sim 26.10\%$



2018

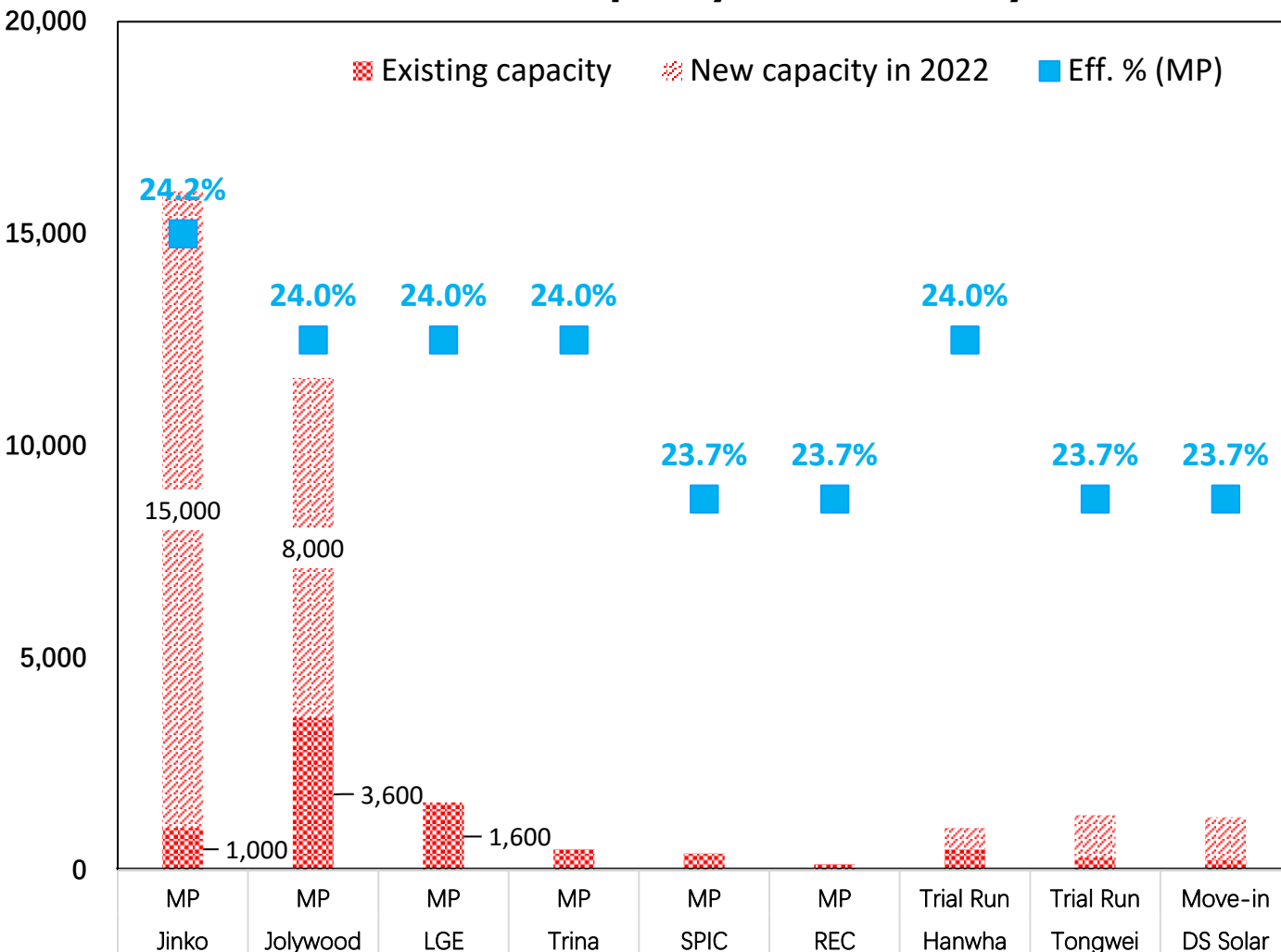
2020



Full-area TOPCon emitter  
2020, Fraunhofer ISE  
TOPCon,  $\eta \sim 26.0\%$

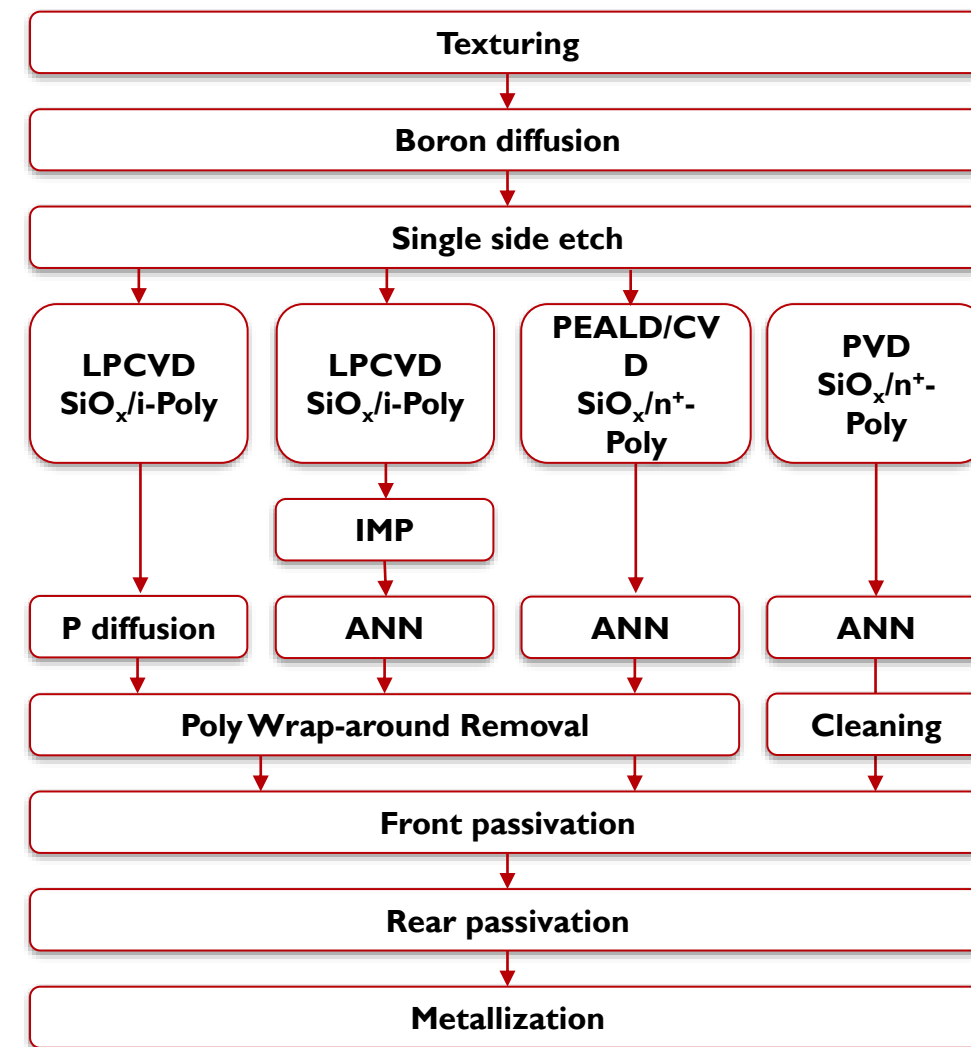
# Industry progress of TOPCon technology

2022F TOPCon Capacity and Efficiency\*, Unit: MW, %



\*Data from PV Infolink

24.6%  
24.4%  
24.2%  
24.0%  
23.8%  
23.6%  
23.4%  
23.2%  
23.0%



Jinko, Trina

Jolywood 1.0

Tongwei / Suntech / Runyang

Jolywood 2.0

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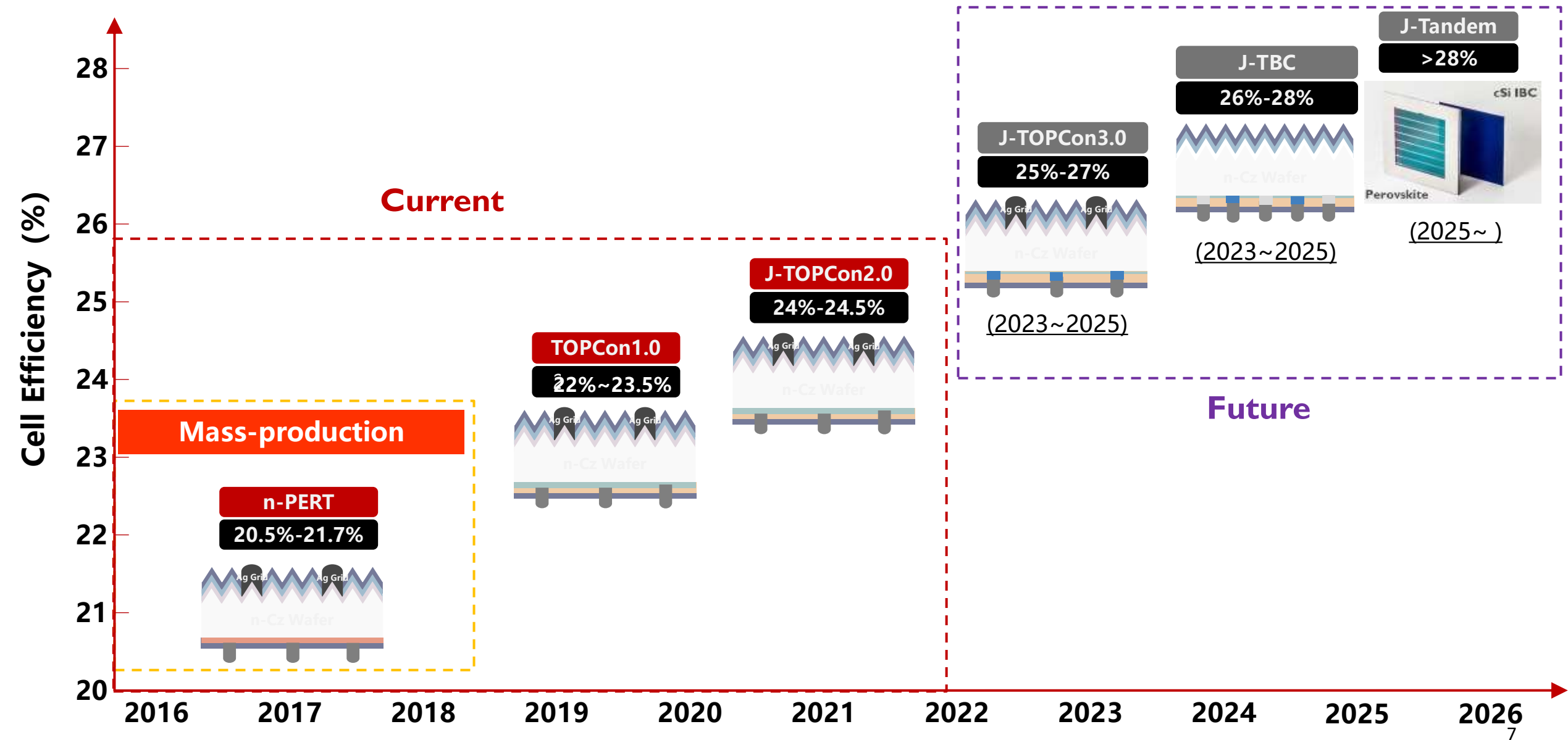
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**Jolywood TOPCon 2.0 Product**

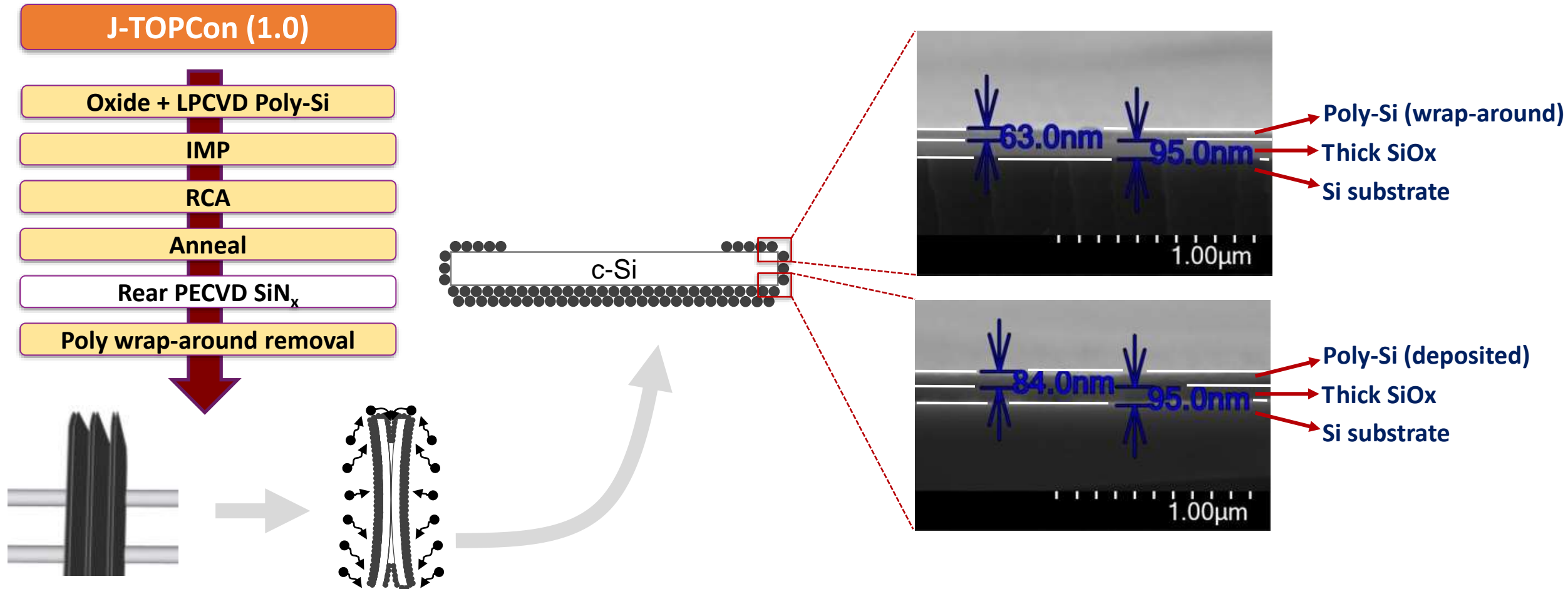
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# Jolywood technology roadmap



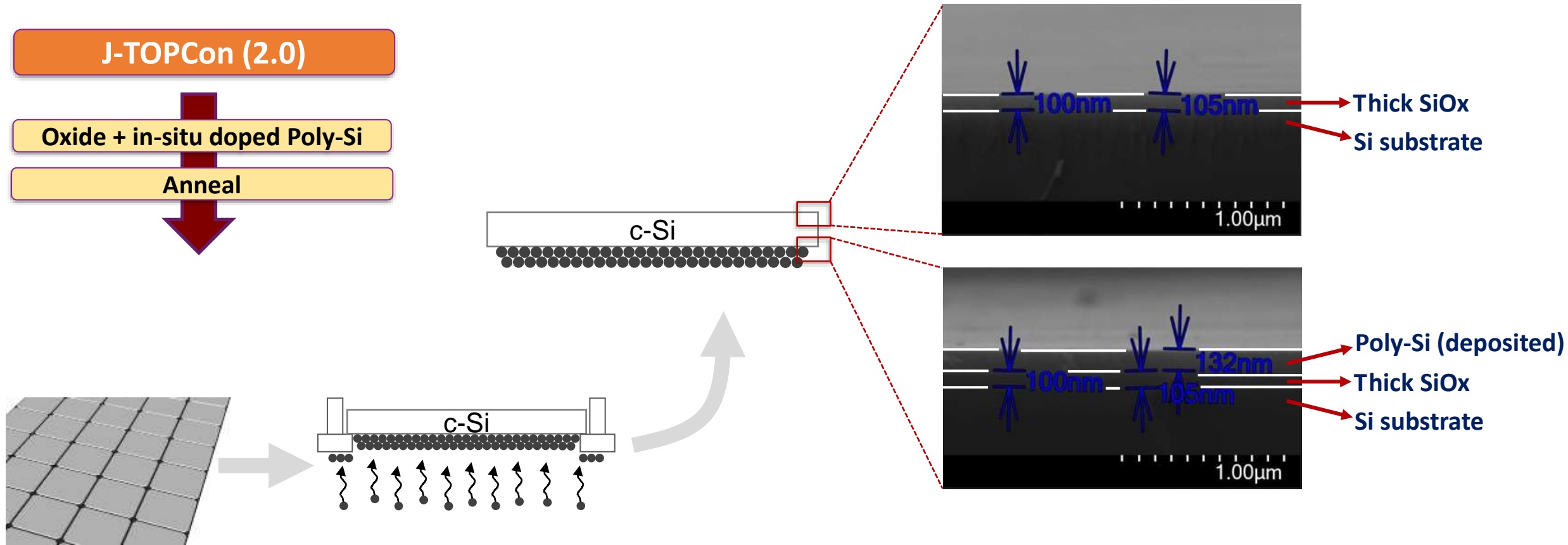
# Unavoidable wrap-around poly Si with TOPCon 1.0



- Unavoidable poly-Si wrap-around during LPCVD poly deposition
- Additional wrap-around removal is necessary and led to low yield and high cost

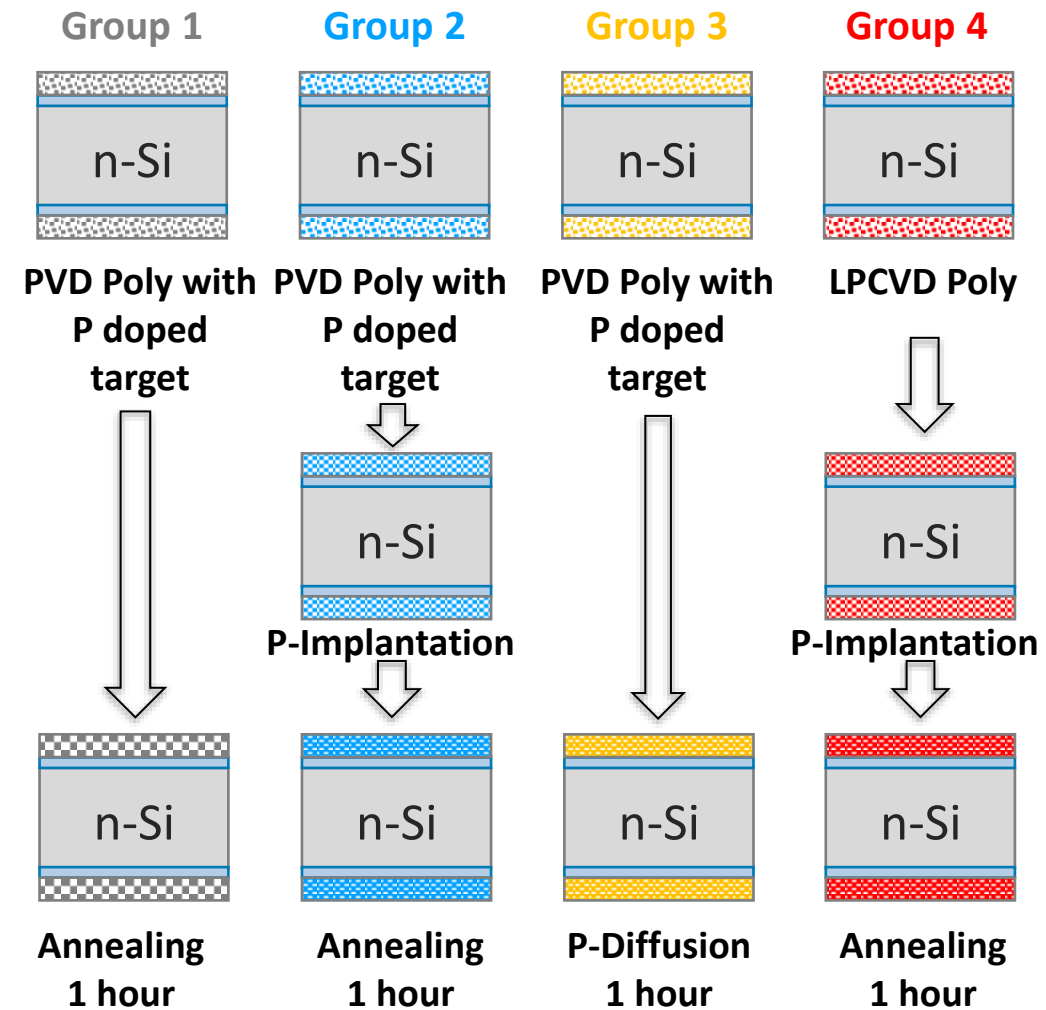
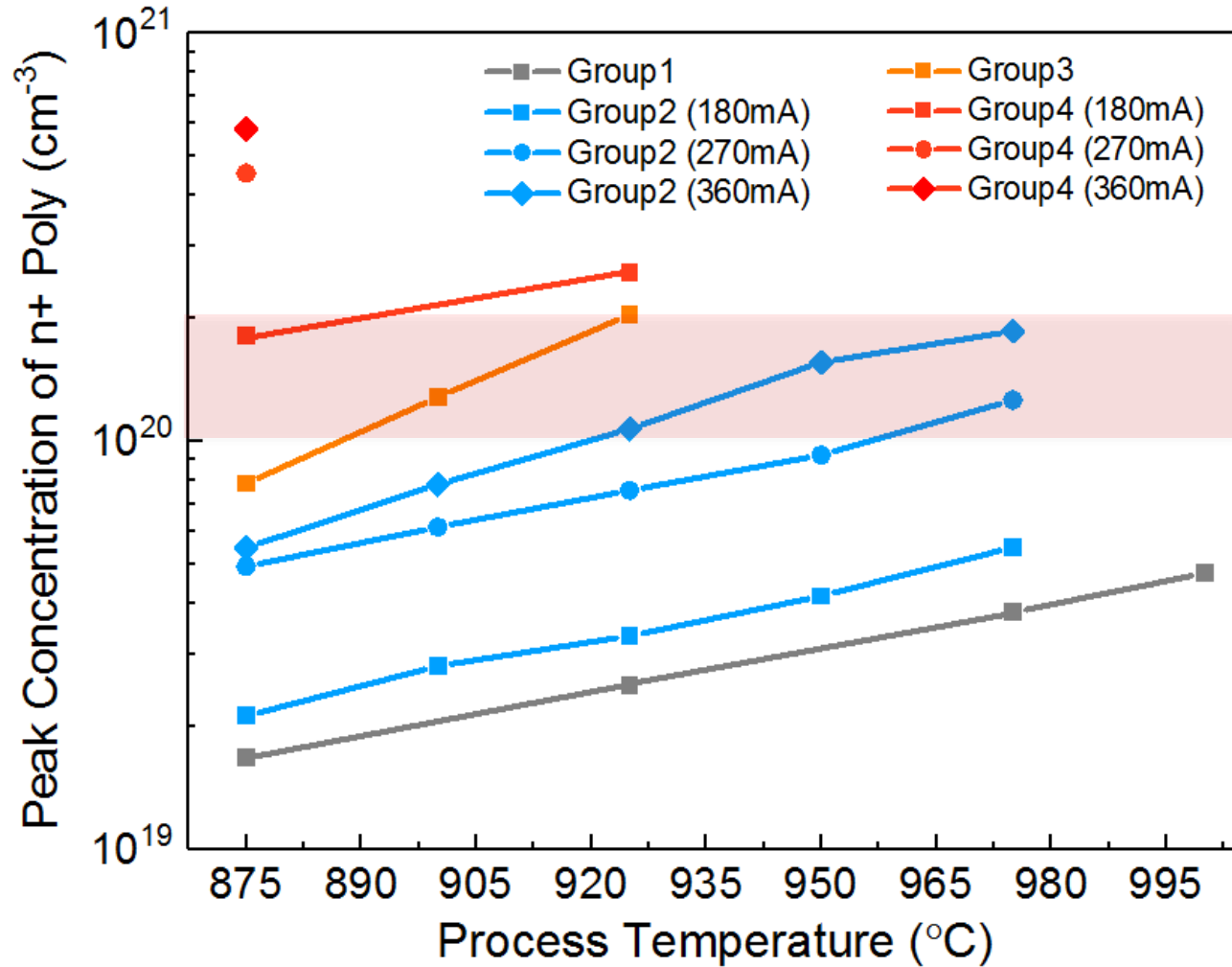


# No wrap-around poly Si with TOPCon 2.0



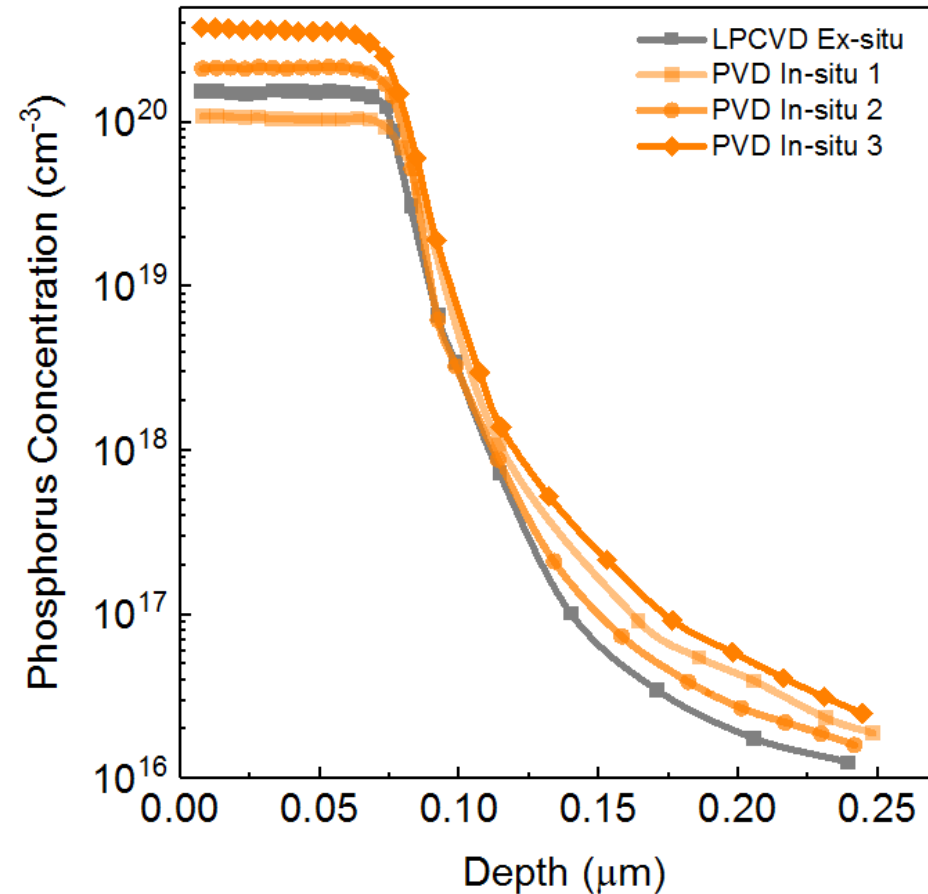
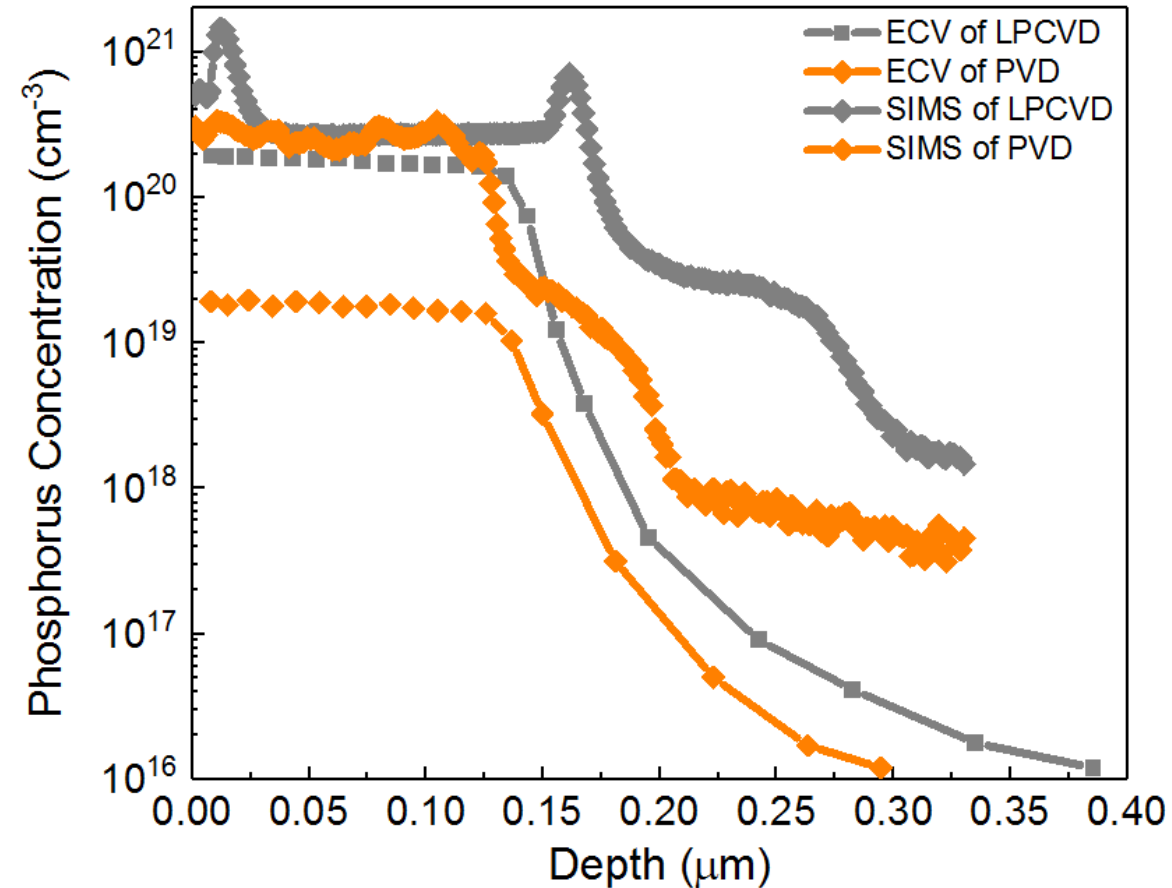
- No wrap-around of poly Si with plate-type PVD process
- No wrap-around removal required, led to shorter process flow and higher yield

# Challenge to reach high doping concentration

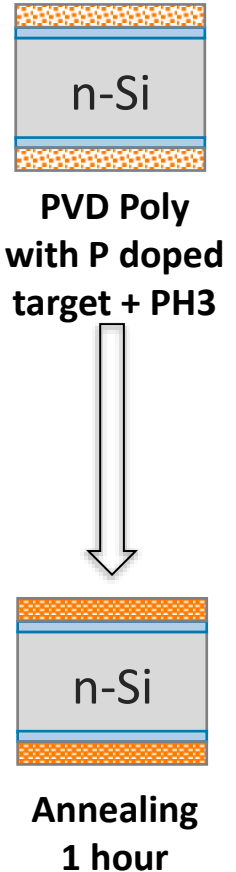


- Difficult to reach high doping level ( $> 1e^{20} \text{ cm}^{-3}$ ) using ONLY p-doped target during PVD process

# Tunable doping concentration achieved

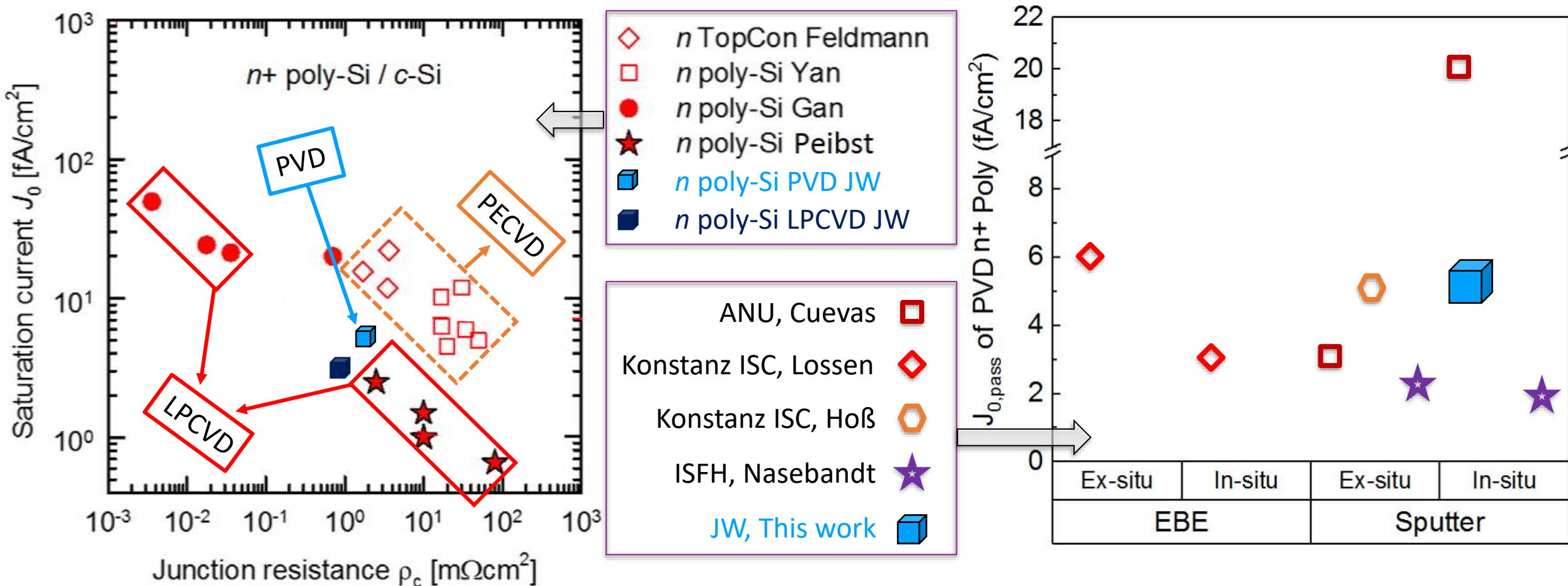


Group 5



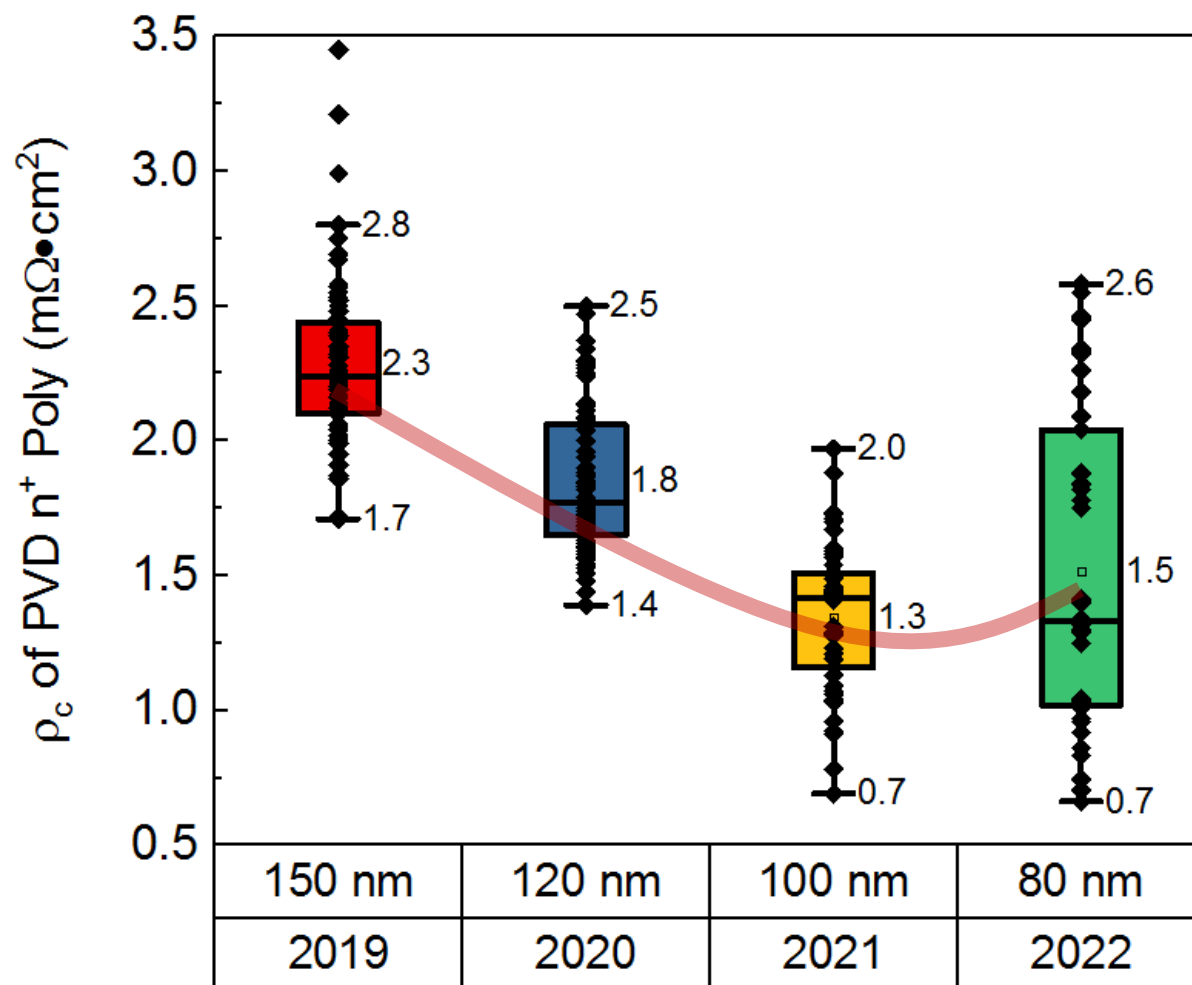
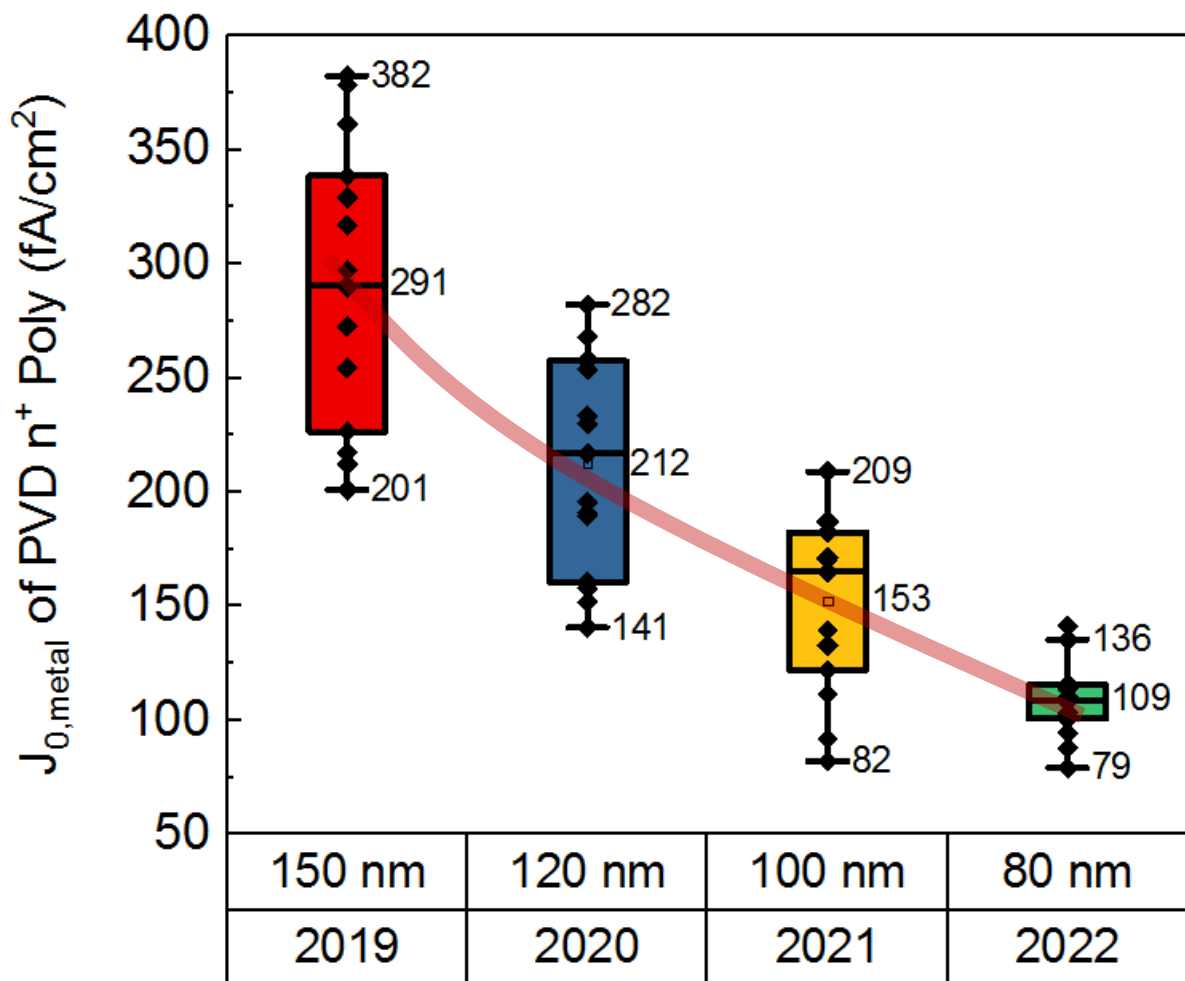
- Challenge to activate the phosphorous atoms from the doped target
- Tunable doping concentration achieved with additional PH<sub>3</sub> during deposition process

# Low $J_{0pass}$ and $\rho_c$ achieved in production line



- Similar  $J_{0pass}$  and  $\rho_c$  achieved using PVD deposited n<sup>+</sup> poly compared with LPCVD n<sup>+</sup> poly

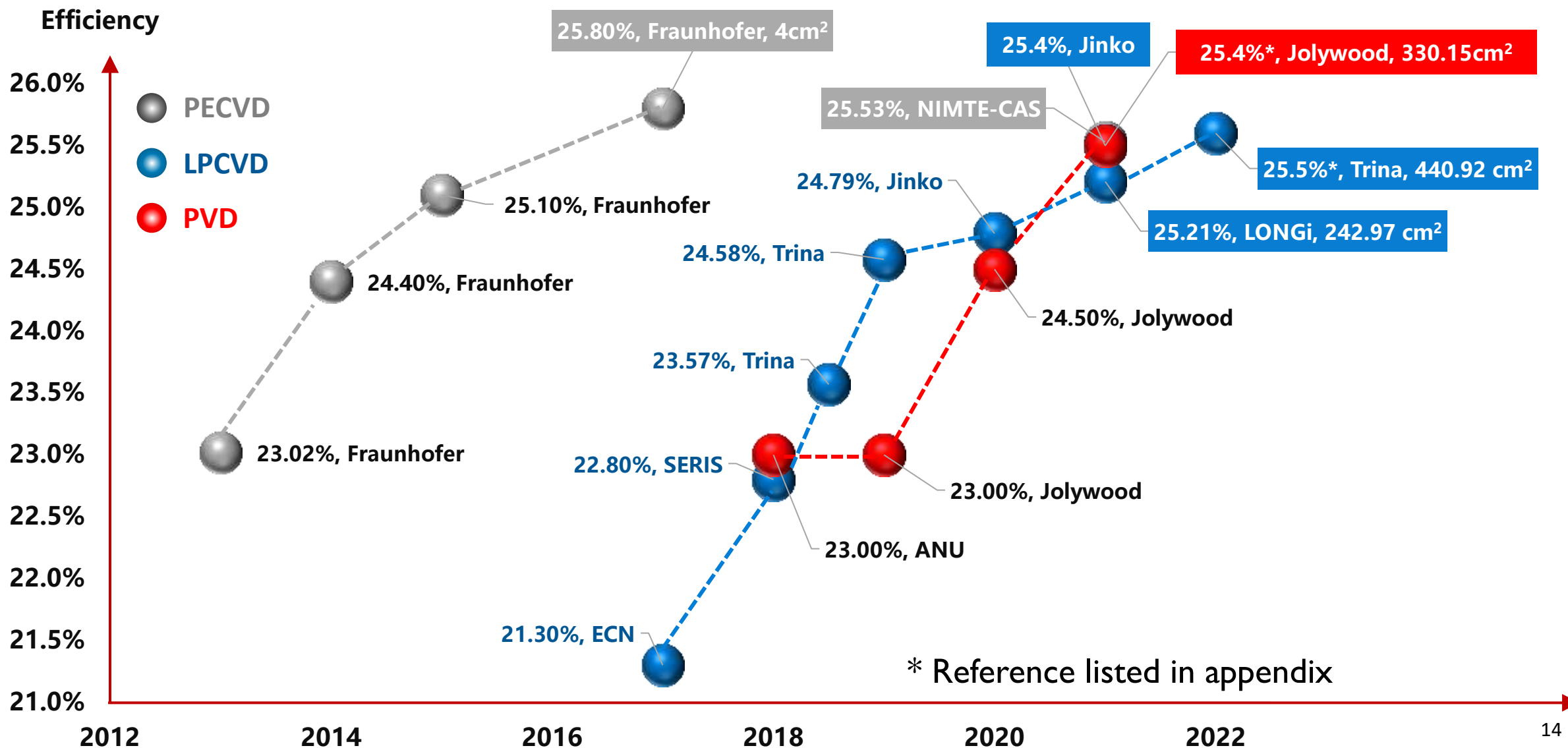
# Low $J_{0,metal}$ and $\rho_c$ with different poly thickness



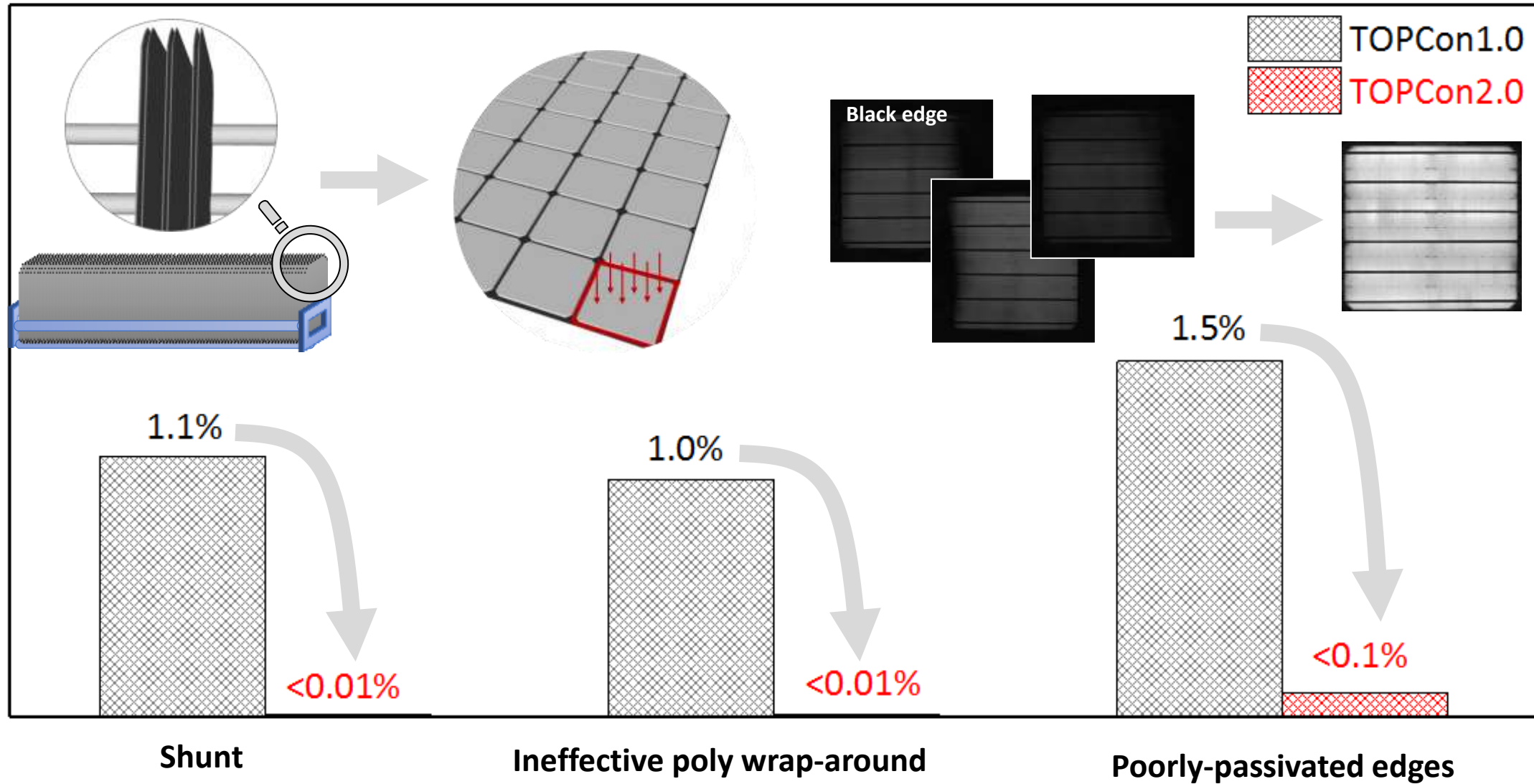
- Good contact formed on PVD deposited  $n^+$  poly with 100nm thickness in production line and 80nm in pilot-line

# Lab-efficiency achieved with various poly depositions

The reported lab-efficiency of TOPCon solar cells with various poly deposition methods

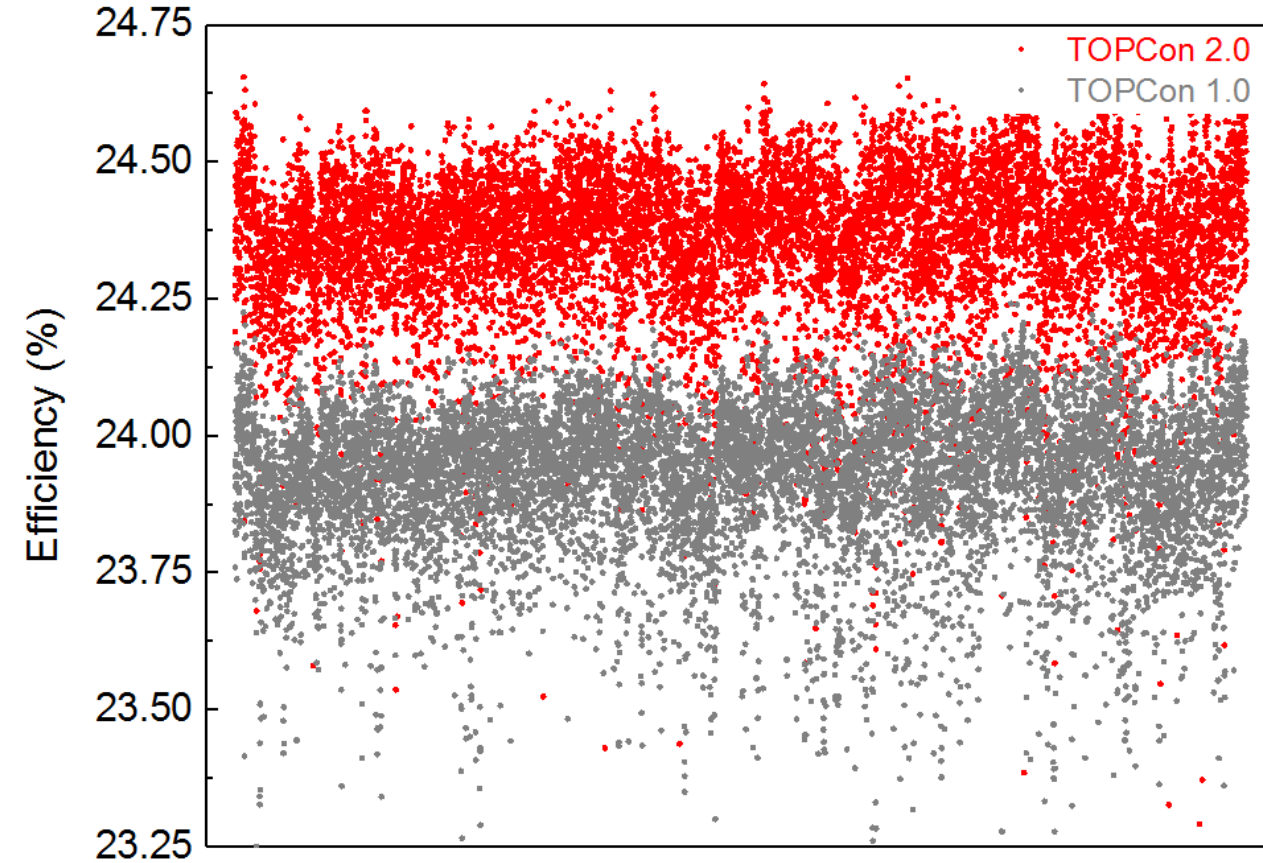
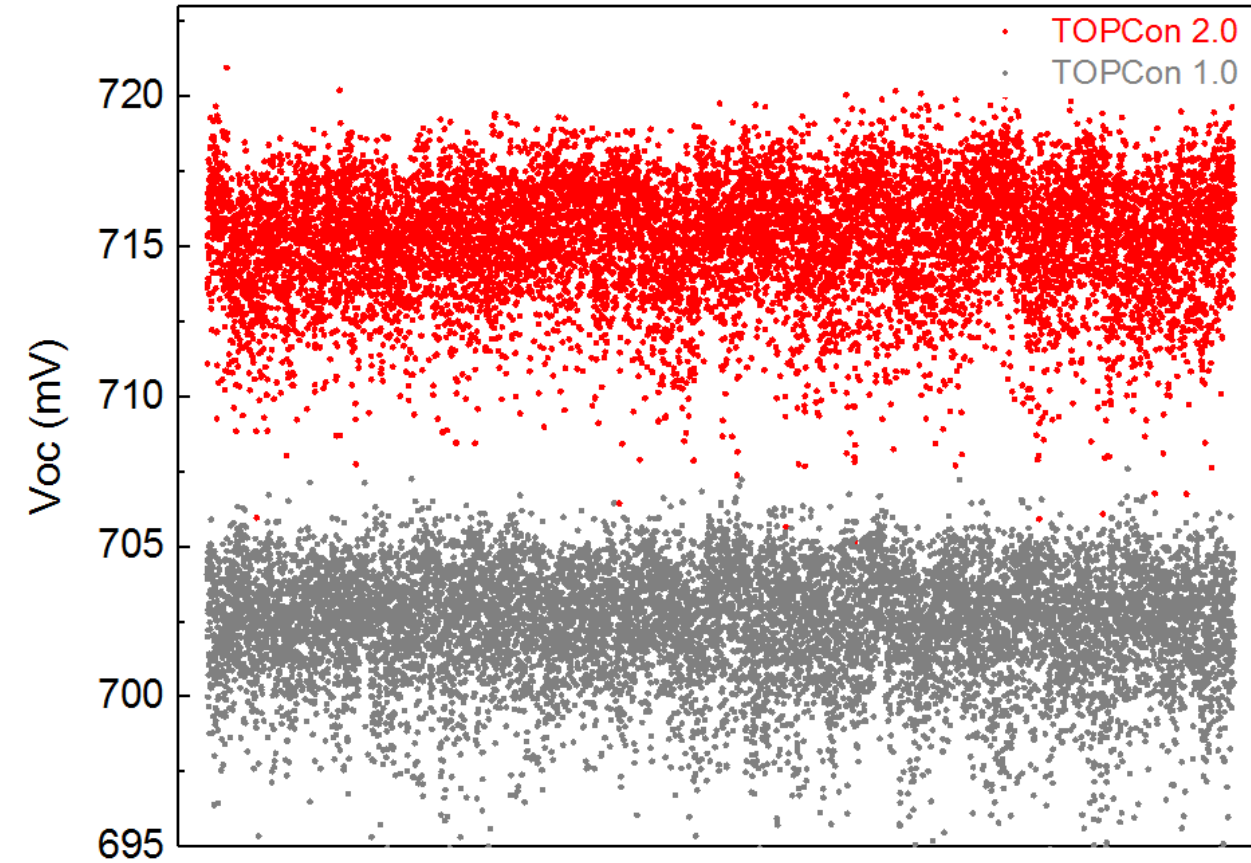


# Yield improvement with TOPCon 2.0



- Yield significantly improved from TOPcon 1.0 to TOPCon 2.0

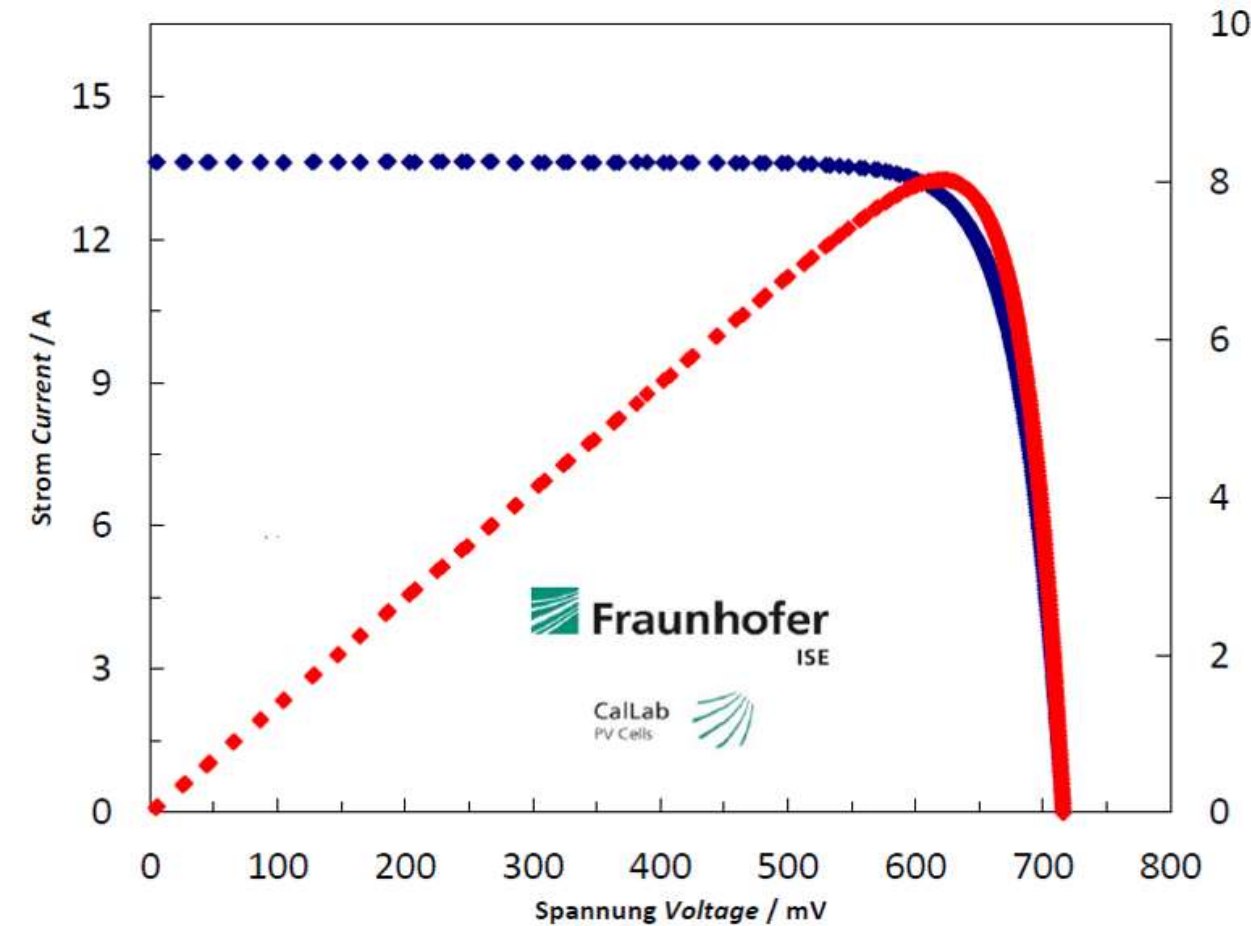
# Voc and Eff improved from TOPCon 1.0 to 2.0



- Efficiency and open-circuit voltage significantly improved from TOPCon 1.0 to TOPCon 2.0



# Voc and Eff improved from TOPCon 1.0 to 2.0

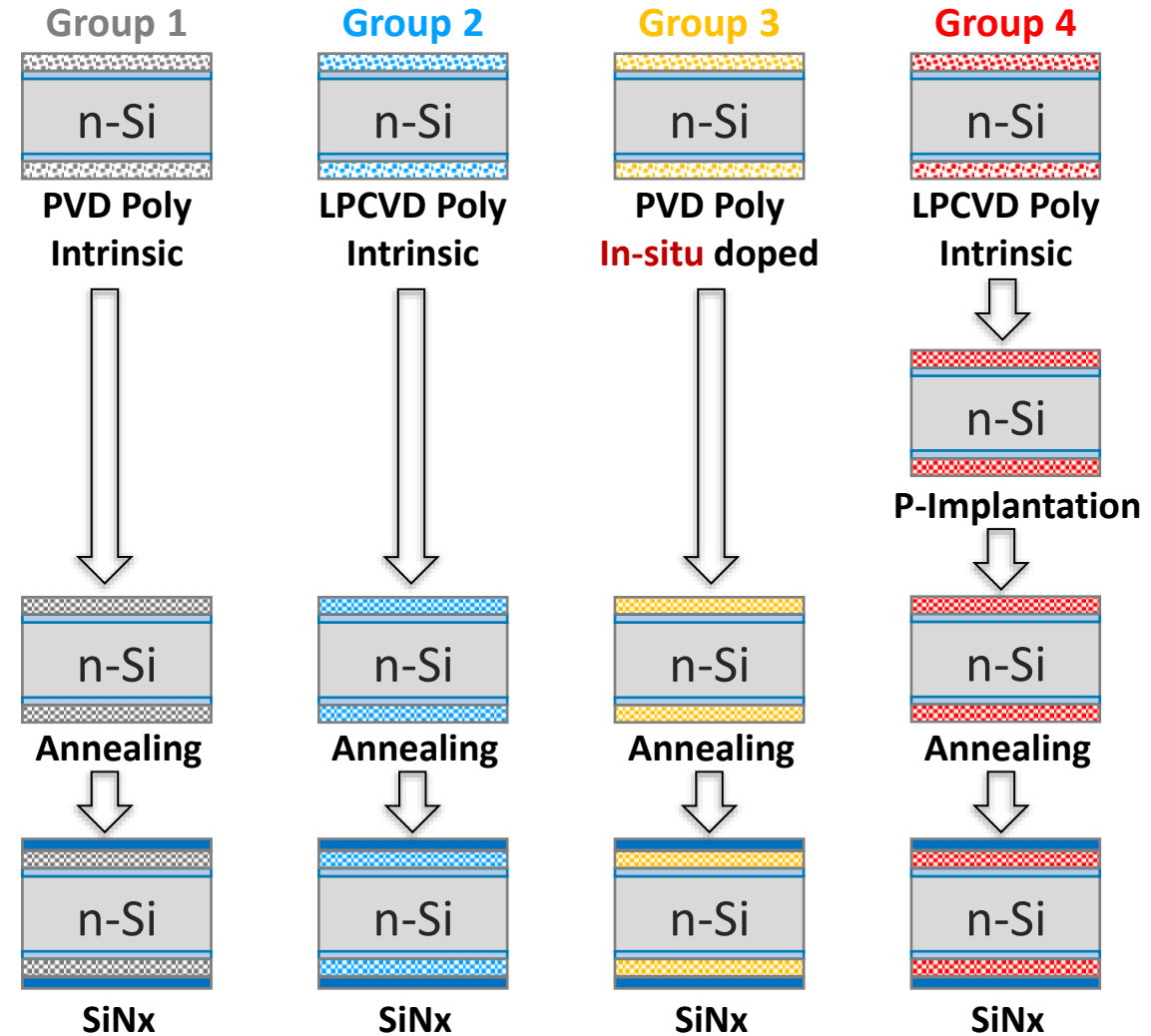
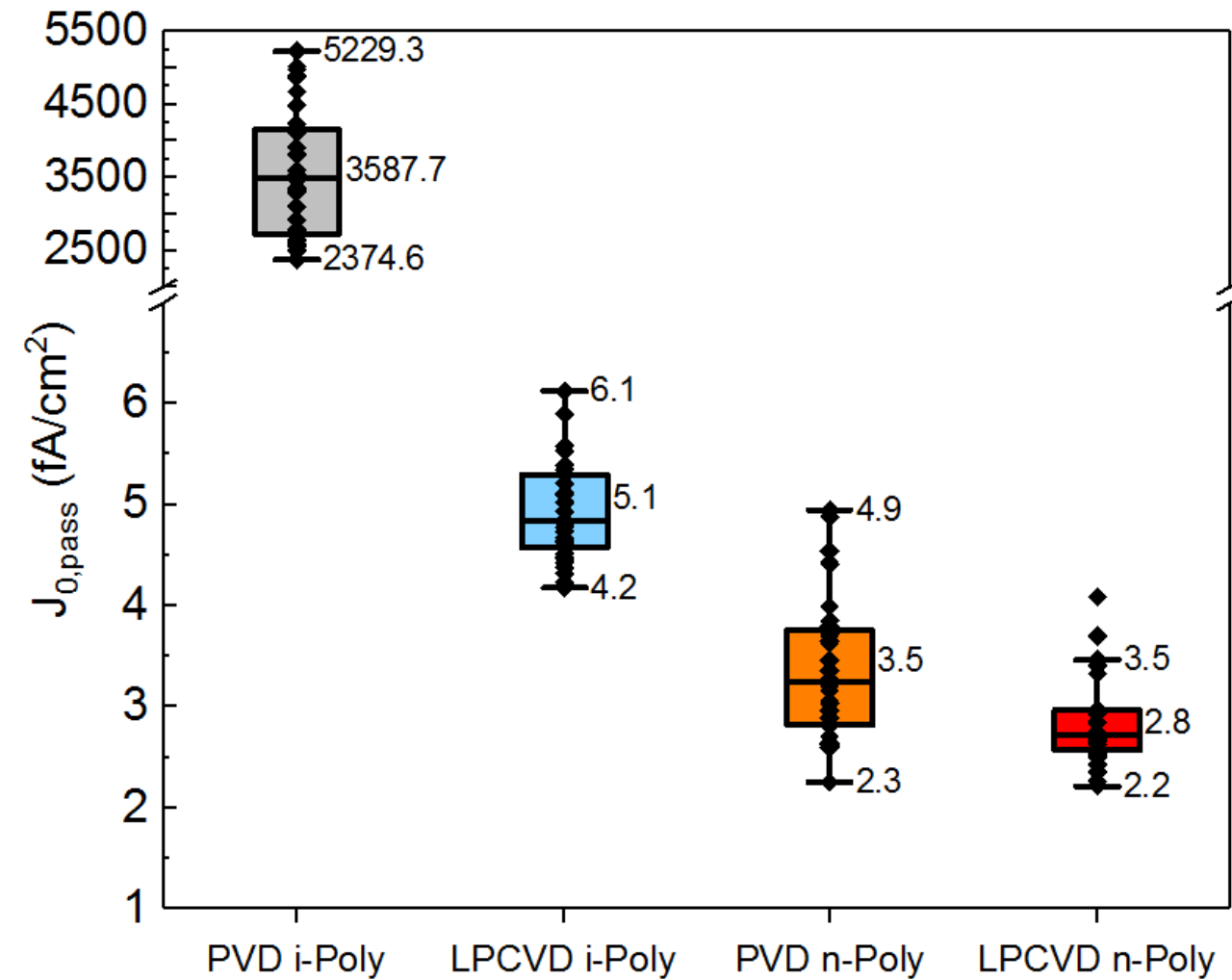


Fläche / Area (t) <sup>1</sup> :	=	( 330.21 ± 0.33 )	cm <sup>2</sup>
$V_{OC}$	=	( 715.9 ± 2.3 )	mV
$I_{SC}$ (Ed.4 - 2019) /2/	=	( 13.62 ± 0.19 )	A
$J_{SC}$	=	( 41.25 ± 0.58 )	mA/cm <sup>2</sup>
$I_{MPP}$	=	12.94	A
$V_{MPP}$	=	620.6	mV
$P_{MPP}$	=	( 8.03 ± 0.16 )	W
$FF$	=	( 82.3 ± 1.2 )	%
$\eta$	=	( 24.32 ± 0.49 )	%

M10 Size	Jsc	Uoc	FF	Eta	Area
Unit	[mA/cm <sup>2</sup> ]	[mV]	[%]	[%]	[cm <sup>2</sup> ]
Jolywood	41.32	716.6	82.75	24.50	330.15
Fraunhofer ISE	41.25	715.9	82.3	<b>24.32</b>	330.21

- Similar Eff and Voc measured in the production line and certified by Fraunhofer CalLab

# Further improvement



- Possible sputtered damage causes higher  $J_{0,pass}$  with PVD i-poly compared with LPCVD i-poly

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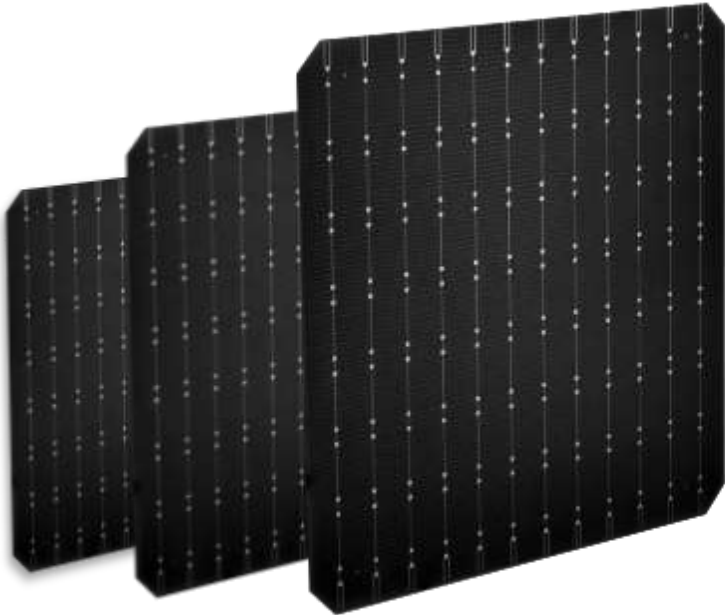
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**Jolywood TOPCon 2.0 Module**

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**Outlook**

## TOPCon 2.0 + large-size wafer



## TOPCon 2.0 module



High Power ~560-570W

High Bifaciality ~80%

Low Temperature Coefficient ~-0.31%/K

Low Degradation

High Reliability

New POPAID technology

Large Size Wafer

- About 3% BOS cost reduction and 4-5% energy yield achieved with J-TOPCon 2.0 modules compared with p-PERC bifacial modules\*

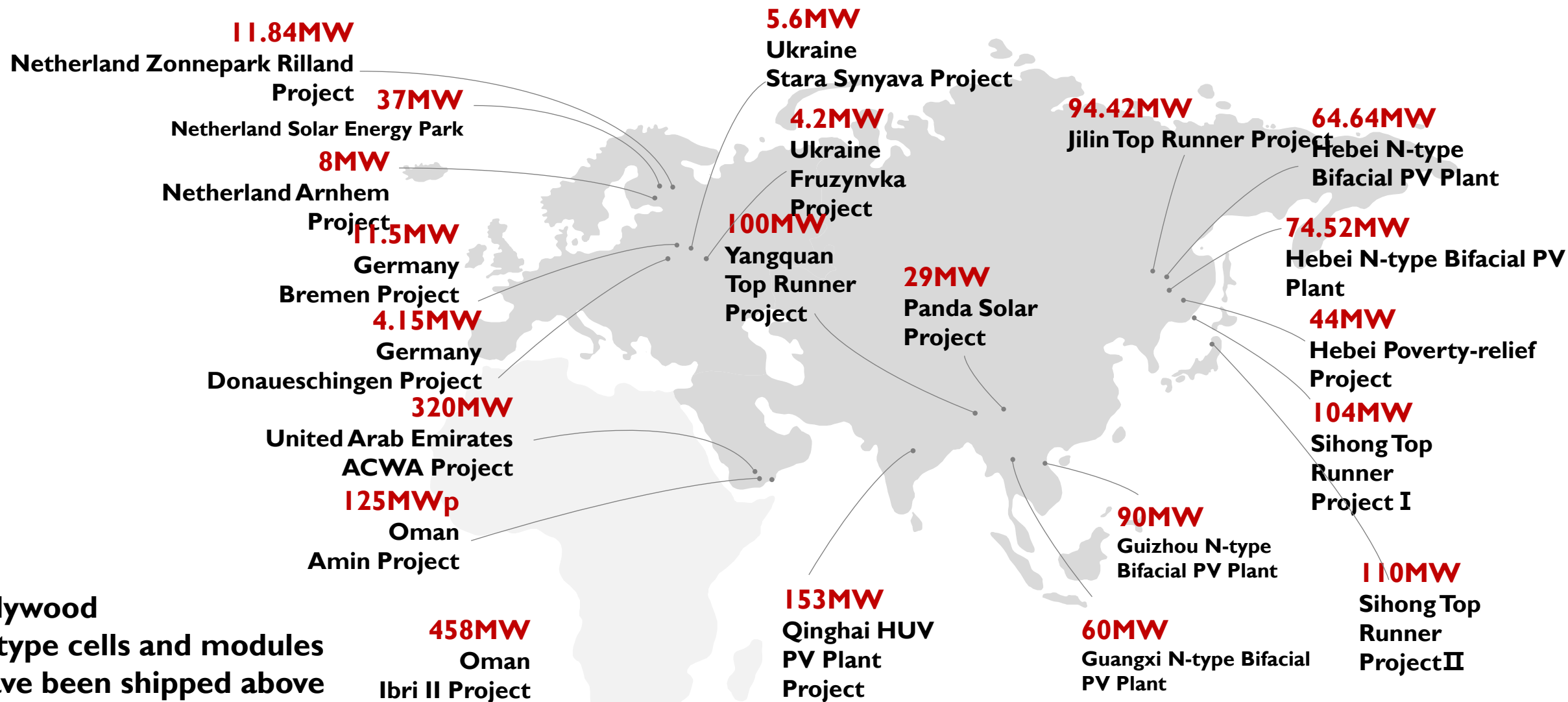
\*Calculation varies from case to case depending on the actual application

# LCOE Calculation

	PERC - M10	TOPCon - M10	unit
Module Power	540	560	Wp
Module Size	2278*1134	2278*1134	mm
Efficiency	20.91	21.68	%
Bifaciality	70	80	%
P <sub>mpp</sub> Temper. Coeff	-0.35%	-0.31%	/°C
1 <sup>st</sup> year Degradation	2	1	%
Annual Degradation	0.45%	0.40%	/yr
Specific production	1150	1200	kWh/kW <sub>p</sub> /yr
<b>Module cost</b>	<b>29.06</b>	<b>32.36</b>	
BOS cost	26.30	25.66	¢/Wp
CAPEX cost	55.36	58.02	
<b>LCOE</b>	<b>3.17</b>	<b>3.17</b>	<b>US ¢/kWh</b>

- Up to ~11% price premium possible with Jolywood TOPCon 2.0 modules due to its higher module power and higher electricity generation per wattpeak

# Outstanding n-type Shipment



Jolywood  
n-type cells and modules  
have been shipped above

**5GW** globally

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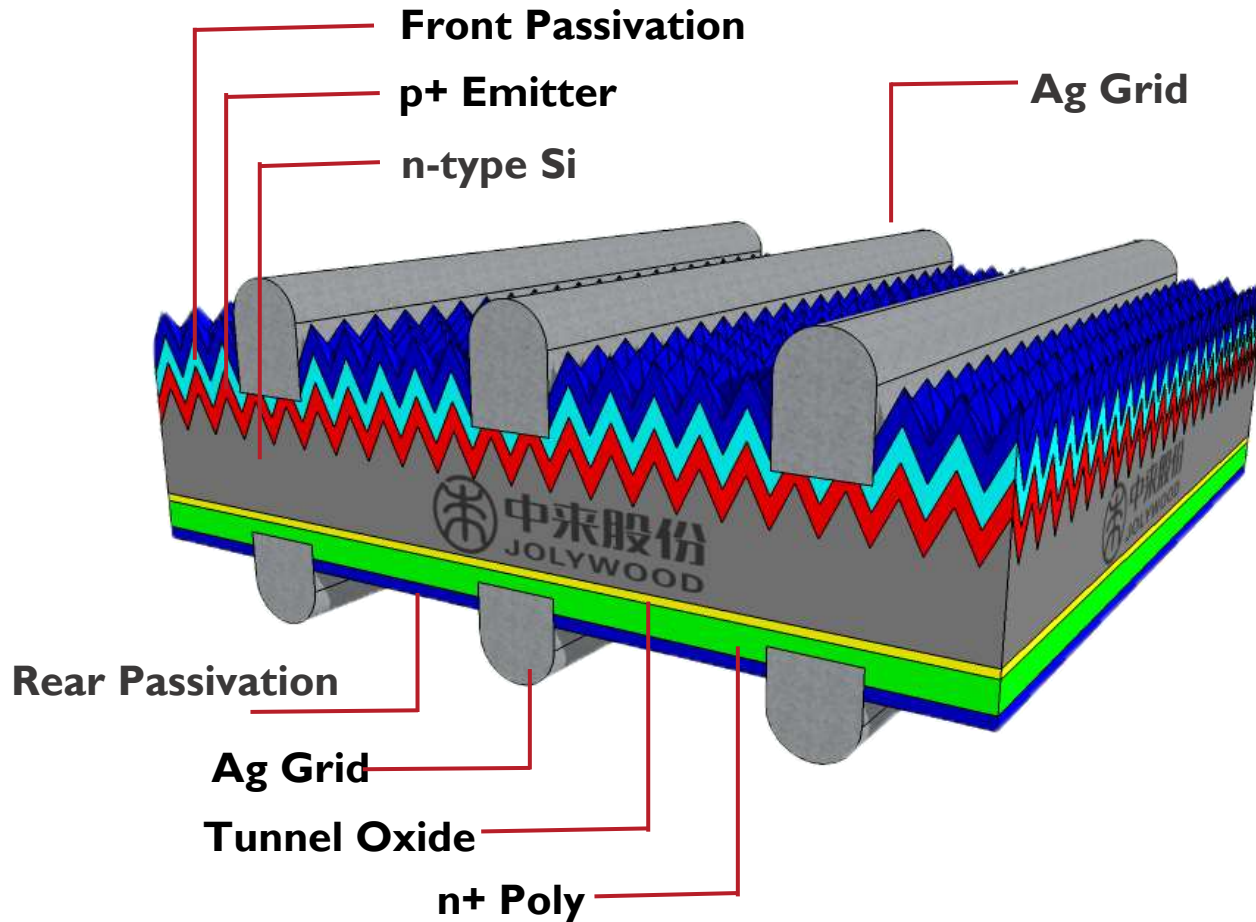
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# What's next?



## Efficiency Improvement:

- Highest efficiency loss at emitter contact
- Improved emitter contact required with limited high-temperature steps and time
- Selective emitter necessary?

## Cost reduction:

- Highest cost difference compared with PERC attributed to higher Ag consumption
- Revolutionary approaches required to reduce Ag consumption

## JW TOPCon 2.0 → JW TOPCon 3.0:

The same efficiency and BB no, conventional screen-printing, but at least 1/3 less Ag



# THANK YOU

**It's always darkest before dawn. Keep the faith!**

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